

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) Method for producing an irreversible storage medium comprising an array of memory cells ~~(3)~~, each memory cell ~~(3)~~ comprising one zone ~~(10)~~ of an active layer ~~(8)~~ arranged between first ~~(1)~~ and second ~~(2)~~ conductors, binary information stored in the memory cell ~~(3)~~ being determined by the electrical conducting state of the corresponding zone ~~(10)~~, method ~~characterized in that it comprises~~ comprising assembly of a blank storage medium having an active layer ~~(8)~~ which is in an initial insulating state, production of a stamping die ~~(17)~~ having a stamping pattern that corresponds to the information to be stored, and stamping of the storage medium using the stamping die ~~(17)~~ so as to make predetermined zones ~~(10)~~ of the active layer ~~(8)~~ electrically conductive by means of localised plastic deformation ~~(4)~~.

2. (Currently Amended) Method according to claim 1, ~~characterized in that~~ wherein the active layer ~~(8)~~ is formed by a charged resin.

3. (Currently Amended) Method according to ~~one of the claims 1 and 2~~ claim 1, ~~characterized in that~~ wherein assembly of a blank storage medium successively comprises

- deposition, on a substrate ~~(5)~~, of a first conducting layer ~~(11)~~ and of two oppositely doped semi-conducting layers ~~(6, 7)~~,
- etching of the stack formed by the first conducting layer ~~(11)~~ and the two semi-conducting layers ~~(6, 7)~~, so as to obtain a first array of parallel strips ~~(13)~~,

- filling the space between the strips ~~(13)~~ of the first array of parallel strips ~~(13)~~ so as to create a common plane with the strips ~~(13)~~ of the first array of parallel strips ~~(13)~~,
 - deposition of the active layer ~~(8)~~ on said common plane,
 - deposition of a second conducting layer on the active layer ~~(8)~~,
- etching of the second conducting layer, so as to obtain a second array of parallel strips perpendicular to the strips ~~(13)~~ of the first array of strips ~~(13)~~,
- filling the space between the strips of the second array of parallel strips.

4. (Currently Amended) Method according to claim 3, ~~characterized in that~~ wherein the space between the strips of the first and/or second array of parallel strips is filled by means of a technique using a planarization resin ~~(12, 9)~~.

5. (Currently Amended) Method according to claim 3, ~~characterized in that~~ wherein the space between the strips of the first and/or second array of parallel strips is filled by means of a mechanical-chemical polishing step.

6. (Currently Amended) Method according to ~~any one of the claims 1 to 5~~ claim 1, ~~characterized in that~~ wherein production of the stamping die ~~(17)~~ successively comprises

- deposition of a photoresist ~~(14)~~ on an intermediate substrate ~~(15)~~,
- etching, in the photoresist ~~(14)~~, of an array of elementary zones ~~(16)~~ having a configuration corresponding to the stamping pattern,
- electrolytic deposition, on the intermediate substrate ~~(15)~~ and the photoresist ~~(14)~~, of a metal constituting the stamping die ~~(17)~~,
- detachment of the stamping die ~~(17)~~ from the intermediate substrate ~~(15)~~,
- removal of the residues of photoresist ~~(14)~~ from the stamping die ~~(17)~~.

7. (Currently Amended) Irreversible storage medium, ~~characterized in that it is~~
obtained by means of a method according to ~~any one of the claims 1 to 6~~claim 1.